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## PATENT AND TRADEMARK OFFICE

## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

APPLICANT

Toshiya Yokogawa et al.

FILING DATE

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11/1/2001

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Sheet 1 of 1

## U.S. PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.						

## FOREIGN PATENT DOCUMENTS

Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	No
1.	PC	EP 0 309 290 A1	03/29/1989	Europe			

## OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

Ref. Desig.	Examiner's Initials	
1.	PC	A. Konstantinov et al., "Investigation of Lo-Hi-Lo and Delta-Doped Silicon Carbide Structures", Mat. Res. Soc. Symp. Proc., Vol. 640, 2001, pp. H2.4.1-H2.4.6.
2.	PC	D.W. van der Weide, "Delta-doped Schottky diode nonlinear transmission lines for 480-fs, 3.5-V transients", Applied Physics Letters, Vol. 65, No. 7, 15 August 1994, pp. 881-883.
3.	PC	S M Bedair, "Selective-area and sidewall growth by atomic layer epitaxy", Semiconductor Science and Technology, Vol. 8, No. 6, 1 June 1993, pp. 1052-1062.
4.	PC	Shui Jinn WANG et al., "Schottky/Two-Dimensional Hole Gas Silicon Barrier Diodes with Single and Coupled Delta-Doped Wells", Jpn. J. Appl. Phys., Vol. 33, No. 4B, Part 1, 1 April 1994, pp. 2429-2434.
5.	PC	W.C. Hsu et al., "A Quantum Well $\delta$ -Doped GaAs Fet Fabricated by Low-Pressure Metal Organic Chemical Vapor Deposition", Solid-State Electronics, Vol. 34, No. 6, 1 June 1991, pp. 649-653.

Examiner: PHAT X. CAO

Date Considered: 7/22/03

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